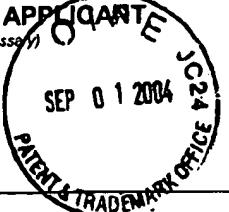


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		Application Number	09/945,554
		Filing Date	August 30, 2001
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2826
		Examiner Name	Dickey, Thomas
Sheet 1 of 1		Attorney Docket No: 1303.028US1	

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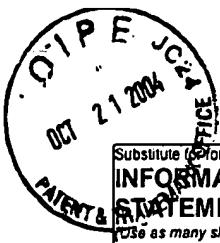
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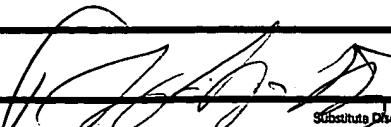
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